Atty. Dkt. No. 039153-0683 (H1721)

Amendments to the Specification:

Please amend the specification as follows:

Please replace paragraph starting at page 1, paragraph number [0001], with the following rewritten paragraph:

[0001] The present invention is related to integrated circuit (IC) substrates or wafers and to processes of making IC substrates or wafers. More particularly, the present invention relates to a method of forming strained semiconductor structures on substrates and to strained semiconductor structures or layers.